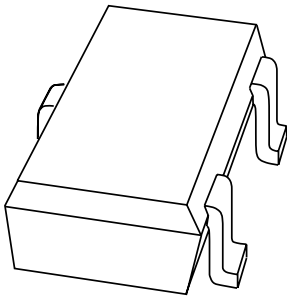


# DATA SHEET



**BFS20W**

**NPN medium frequency transistor**

Product data sheet

1999 Apr 21

# NPN medium frequency transistor

# BFS20W

### FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 20 V).
- Very low feedback capacitance (typ. 350 fF).

### APPLICATIONS

- IF and VHF applications in thick and thin-film circuits.

### DESCRIPTION

NPN medium frequency transistor in a SOT323 (SC-70) plastic package.

### MARKING

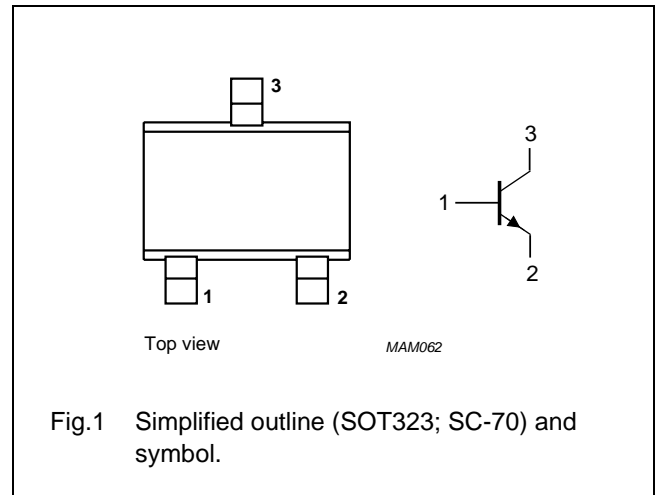
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BFS20W	N1*

### Note

- \* = -: Made in Hong Kong.  
\* = t: Made in Malaysia.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	30	V
$V_{CEO}$	collector-emitter voltage	open base	-	20	V
$V_{EBO}$	emitter-base voltage	open collector	-	4	V
$I_C$	collector current (DC)		-	25	mA
$I_{CM}$	peak collector current		-	25	mA
$I_{BM}$	peak base current		-	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	-	200	mW
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		-	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

### Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

## NPN medium frequency transistor

BFS20W

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

## Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

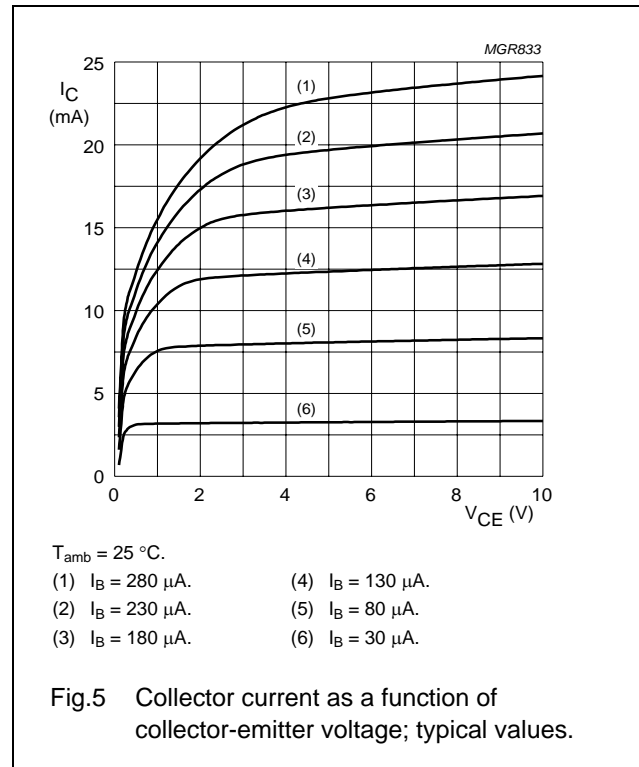
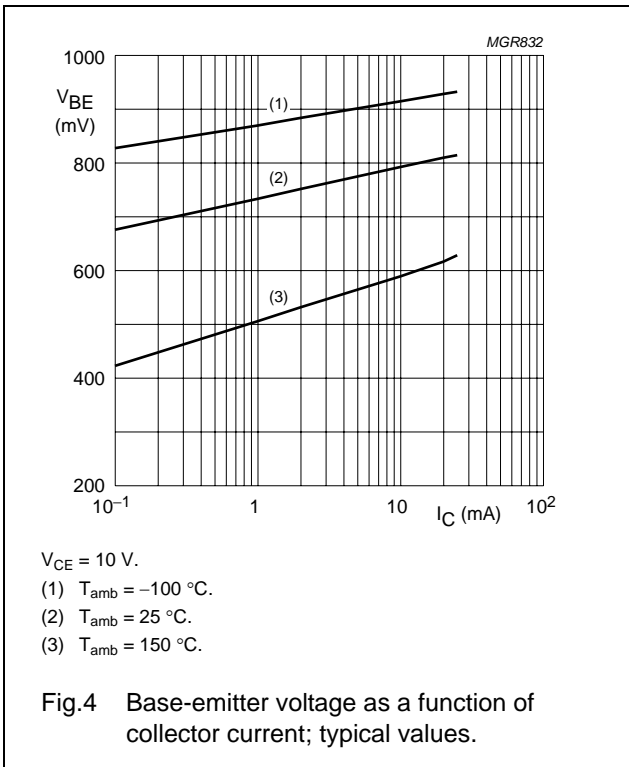
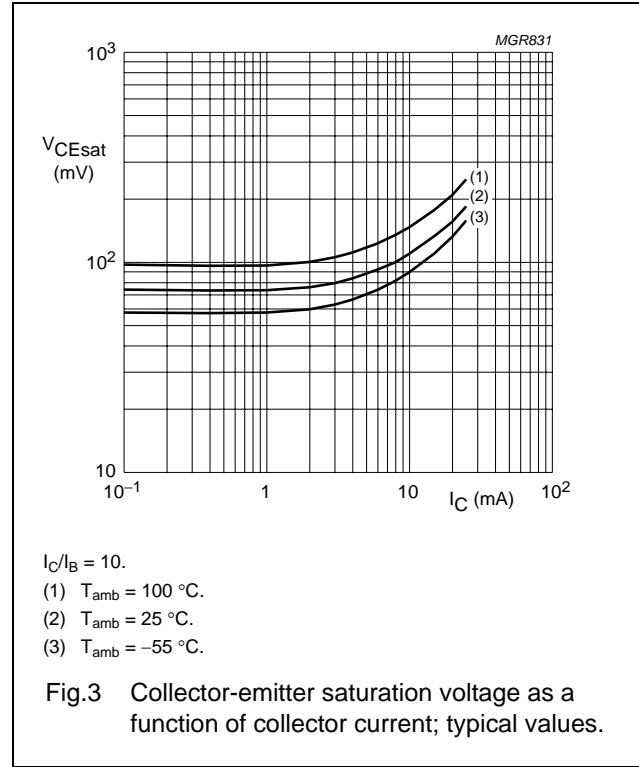
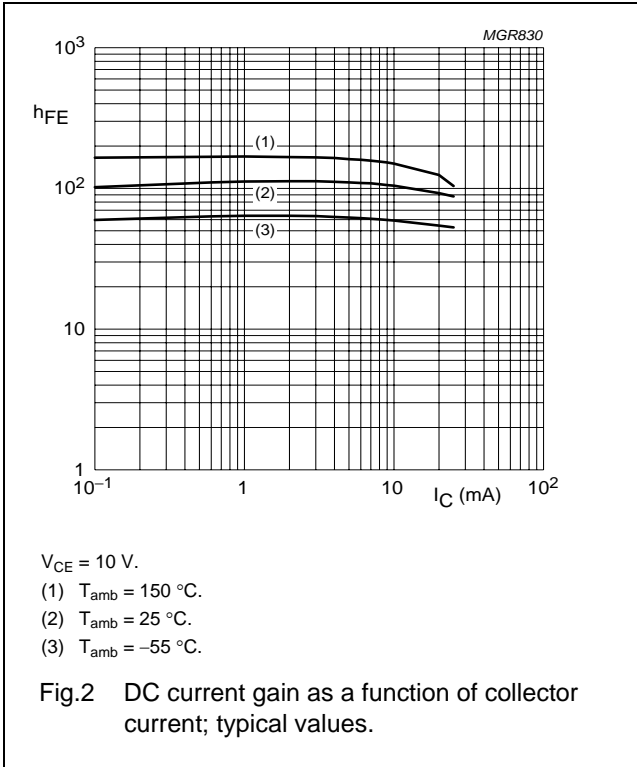
## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 100\text{ °C}$	–	–	10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain	$I_C = 7\text{ mA}; V_{CE} = 10\text{ V}$	40	85	–	
$V_{BE}$	base-emitter voltage	$I_C = 7\text{ mA}; V_{CE} = 10\text{ V}$	–	740	900	mV
$C_c$	collector capacitance	$I_E = I_B = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	1	–	pF
$C_{re}$	feedback capacitance	$I_C = 0; V_{CE} = 10\text{ V}; f = 1\text{ MHz}$	–	350	–	fF
$f_T$	transition frequency	$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	360	470	–	MHz

NPN medium frequency transistor

BFS20W



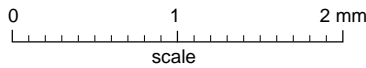
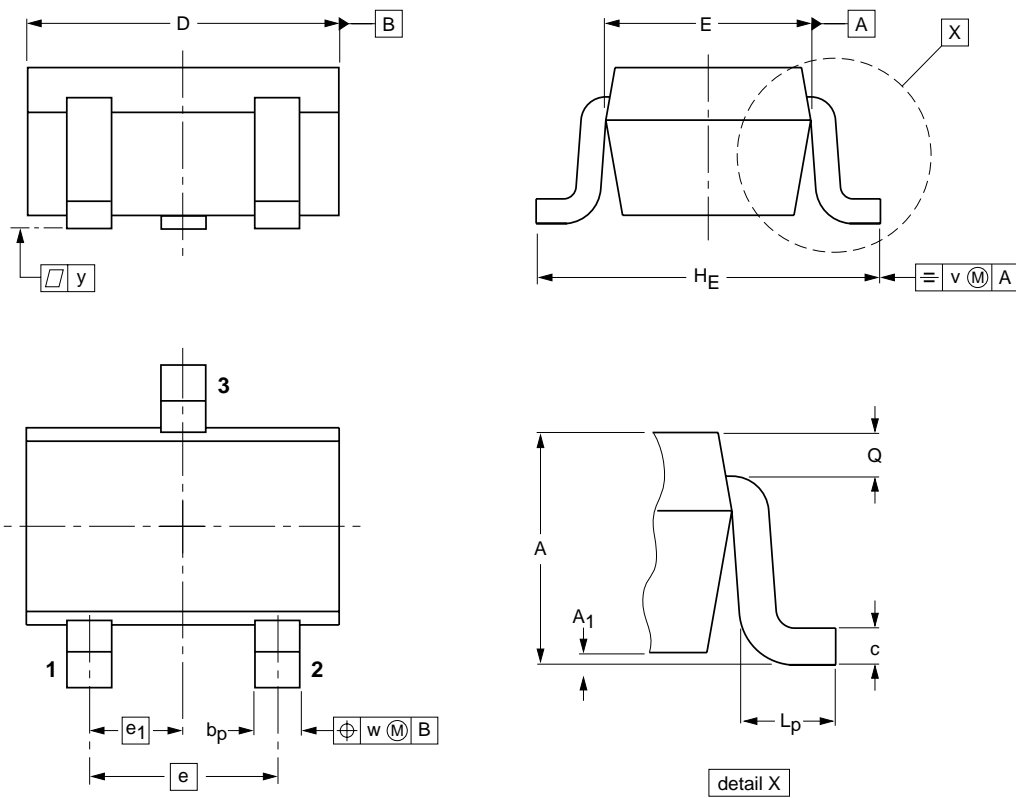
NPN medium frequency transistor

BFS20W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

## NPN medium frequency transistor

BFS20W

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Contact information**

For additional information please visit: **<http://www.nxp.com>**

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Printed in The Netherlands

115002/00/01/pp7

Date of release: 1999 Apr 21

Document order number: 9397 750 05696



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